

REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The Office Action dated March 27, 2006 has been received and its contents carefully reviewed.

By this Response claim 21 has been amended merely to clarify the subject matter recited in the application. No new matter has been added. Claims 1-32 are pending in the application, with claims 1-20 and 22-32 being allowed. Reconsideration and withdrawal of the rejection in view of the above amendments and the following remarks are respectfully requested.

In the Office Action, claim 21 is rejected under 35 U.S.C. § 103(a) as being unpatentable over U.S. Patent No. 6,707,441, issued to Hebiguchi et al. (hereafter “Hebiguchi”) in view of Japanese Publication No. 2000022156, issued to Yamauchi (hereafter “Yamauchi”). Applicants respectfully traverse the rejection because neither Hebiguchi nor Yamauchi, analyzed alone or in any combination, teaches or suggests the combined features recited in the claims of the present application. In particular, Hebiguchi and Yamauchi fail to teach a thin film transistor “wherein the drain electrode has at least two portion having a different width in relation to one another, each of the at least two portions overlapping a gate electrode”, as recited in independent claim 21.

The Office Action concedes that Hebiguchi “fails to disclose the uneven width requirement of the drain electrode.” To remedy this deficient teaching of Hebiguchi, the Office Action relies upon Yamauchi. The Office Action states, with regard to FIG. 3 of Yamauchi, “both uneven portion of the drain electrode, i.e., 102 and 103, overlap the gate electrode 5” (see, page 2 of the Office Action). Applicants respectfully disagree with this analysis of Yamauchi.

Applicants submit Yamauchi discloses, in FIG 3, a TFT having a drain electrode 10 with a horizontally T-shaped part 101. The flat gate electrode 5 includes a base pattern 51 and a top pattern 53 that are joined with a narrow joining part 52 and each side groove 54 (of the gate electrode with a given width is provided on both sides of the joining part 52. Further, Applicants note in the TFT device of Yamauchi, “the source and drain electrodes are formed with the groove 54 in such a way that... lengthwise parts 93 and 103 **do not overlap**” (emphasis added,

see, Solution section of English translation of Patent Abstract of Japan). Accordingly, Applicants submit Yamauchi fails to teach each of the at least two portion (of the drain electrode) overlapping a gate electrode, as recited in claim 21 of the present application.

Because Yamauchi fails to teach at least the above features of claim 21, Yamauchi fails to remedy the deficient teachings of Hebiguchi. Accordingly, no combination of Hebiguchi and Yamauchi provides all the features recited in independent claim 21. Reconsideration and withdrawal of the rejection are respectfully requested.

Applicants believe the foregoing amendments and remarks place the application in condition for allowance and early, favorable action is respectfully solicited.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

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Respectfully submitted,

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